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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: K. SHIMOHIGASHI et al.
Serial No.: 08/448,138
Filed: May 23, 1995
For: SEMICONDUCTOR MEMORY
Group: 2511
Examiner: T. Fears
Batch No.: P55 - Allowed Files

AMENDMENT UNDER 37 CFR 1.312

Honorable Commissioner of
Patents and Trademarks
Washington, D.C. 20231

December 21, 1995

Sir:

In accordance with the provisions of 37 CFR 1.312, please
further amend the above-identified application as follows:

IN THE CLAIMS

Please add the following new claim:

B1
6
-- ~~25~~. A semiconductor memory according to claim ~~24~~,
further comprising:

a fifth switching MOS transistor having a source-
drain path provided between one of said pair of data lines and
a terminal being supplied with said intermediate level
potential; and

69